	ESC	C	[DC	CUMENT	CHANGE REQUEST	
DCR number	1365 Changes required for: General Originator: Steve Thacker						
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED					Secretariat	
Title:	Transistors High F	Power PNP, bas	sed on type E	BUX.	78		
Number:	5204/006		Issue:		6		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)					
Original wording	g:						
As per current p	oublished specifica	tion					
Proposed wordi	ing:						
the listed ESCO		ons, all under E	SCC Generic	-		ethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the G	eneric Specific	ation: Para. 8	3, Te	st Methods and	Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants							
• 2069: for Pov	ver MOSFET Die a	nd packaged V	ariants (to be	e cor	nfirmed by ST by	2020 week 35)	
• No. 20500, Ex	ternal Visual Inspe	ection (Para. 8.6	6): may be rep	plac	ed by: MIL-STD-	750 Test Method 2071 (all types)	
• No. 20900, Ra Method 2076 (a	• • •	ion of Electroni	c Componen	its (F	Para. 8.14): may	be replaced by MIL-STD-750 Test	
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.						
Justification:							

	ESC	C	C	DOCUMENT CHANGE REQUEST					
DCR number	1365	Changes red	quired for: Ge	eneral	Originator: Steve Thacker				
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLE	EMENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.								
Title:	Transistors Low Po	wer PNP, bas	ed on type 2N	2905A					
Number:	5202/002		Issue:	5					
Other documen	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers	Appendix (for STM)								
Original wording	g:								
As per current p	oublished specification	on							
Proposed wordi	ng:								
the listed ESCO	As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix								
	ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.								
For qualification replacement tes • No. 20400, Int • 2072: for Tran	•	ons may be us on (Para. 8.2) aged Variants	sed in place of may be repla	the following ESC	ualified components, the following CC Basic Specifications: 750 Test Method:				
• 2069: for Pov	ver MOSFET Die and	d packaged Va	·	-					
• No. 20500, E>	No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)								



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMEN	TED		
• No. 20900, Radiogra Method 2076 (all type	• •	ion of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	<u>ESC</u>	C	ENT	CHANGE REQUEST				
DCR number	1365	Changes req	uired for: Ge	eneral		Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED							
Title:	Diodes Switching, I	based on types	1N5807 thro	ugh 1N5811				
Number:	5101/013	I	ssue:	6				
Other documen	ts affected:							
5101/014-5, 5101/026-6, 5101/027-5, 5103/029-12, 5103/030-9, 5103/031-10, 5103/032-3, 5103/033-2, 5106/016-10, 5106/017-7, 5106/018-8, 5106/019-9, 5106/020-5, 5106/021-5, 5106/023-4, 5106/024-2, 5201/001-8, 5201/002-10, 5201/003-5, 5201/004-8, 5201/006-6, 5201/011-6, 5201/019-9, 5201/020-1, 5202/001-10, 5202/002-5, 5202/008-7, 5202/014-9, 5203/004-5, 5203/010-9, 5203/011-5, 5203/016-6, 5204/002-9, 5204/006-6, 5205/021-8, 5205/022-7, 5205/023-7, 5205/023-7, 5205/023-7, 5205/029-7, 5207/002-10, 5207/003-5, 5207/005-8, 5207/009-4								
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	g:							
As per current	oublished specification	on						
Proposed word	ing:							
the listed ESCO		ns, all under ES	CC Generic			ethods by Suitable Alternatives review, 000, shall have the following deviations		
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specifica	tion: Para. 8,	Test Method	ds and	Procedures.		
For qualification replacement tes • No. 20400, In • 2072: for Trai • 2078: for Dio	DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)							
• No. 20500, Ex	ternal Visual Inspec	tion (Para. 8.6)	: may be rep	aced by: Mll	L-STD-	750 Test Method 2071 (all types)		
• No. 20900, Ra Method 2076 (a	• • •	on of Electronic	Components	s (Para. 8.14): may	be replaced by MIL-STD-750 Test		
STD-750 Metho	od 2077 (for Power M	MOSFET Die ar	nd packaged	Variants).		ra. 8.3 & 9.5): may be replaced by MIL- Detail Specifications that specifically		

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	ESC	C		DOCUMENT CHANGE REQUEST								
DCR number	1365	Changes re	quired for:	Gen	eral	Originator: Steve Thacker						
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat						
Status: IMPLE	EMENTED											
refer to it.	refer to it.											
Justification:	Justification:											
84th PSWG Mc STM answer is Accordingly, the specification tes Note: there was 5000 to remove Basic specificat	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method. Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.											
Title:	Diodes, Silicon, Pow	er Recitifier	, High Effic	ciency	y, Fast Recovery	based on type BYW81-200						
Number:	5103/029 Issue:				12							
Other documen	ts affected:											
Page:												
as applicable												
Paragraph:												
Manufacturers	Appendix (for STM)											
Original wording	g:											
As per current p	oublished specification	l										
Proposed wordi	ng:											
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix												
ITEMS AFFEC ⁻ Para. 2.1.1, De	TED viations from the Gene	eric Specific	ation: Para.	. 8, Te	est Methods and	Procedures.						
For qualificatior replacement test		ns may be u	sed in place	e of th	ne following ESC	ualified components, the following C Basic Specifications: ′50 Test Method:						

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DCR number 1365 Changes required for: General

Date sent: 2020/07/28

Originator: Steve Thacker

Organisation: ESCC Executive Secretariat

Status: IMPLEMENTED

Date: 2024/02/29

• 2072: for Transistor Die and packaged Variants

• 2078: for Diode Die and packaged Variants

• 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)

• No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)

• No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).

No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).
 Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

DOCUMENT CHANGE REQUEST								
DCR number	1365 Changes required for: General Originator: Steve Thacker							
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat			
Status: IMPLE	MENTED				Georetanat			
Title:	Transistors High I	Power NPN, ba	sed on type 2N	5672				
Number:	5203/004		Issue:	5				
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)						
Original wording	g:							
As per current p	published specifica	tion						
Proposed wordi	ng:							
the listed ESCC		ons, all under E	SCC Generic S		lethods by Suitable Alternatives review, 000, shall have the following deviations			
ITEMS AFFEC Para. 2.1.1, De	TED viations from the G	eneric Specific	ation: Para. 8, ⊺	Fest Methods and	Procedures.			
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants								
• 2069: for Pow	ver MOSFET Die a	nd packaged V	ariants (to be c	onfirmed by ST by	/ 2020 week 35)			
• No. 20500, Ex	ternal Visual Inspe	ection (Para. 8.6	b): may be replay	aced by: MIL-STD	-750 Test Method 2071 (all types)			
	 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 							
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.							
Justification:								

	ESC	C	C	00	CUMENT	CHANGE REQUEST			
DCR number	1365	Changes re	quired for: G	iene	ral	Originator: Steve Thacker			
Date: 2024/02	/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat			
Status: IMPLE	MENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.								
Title:	TRANSISTORS, PO	OWER, MOSF	FET, N-CHAN	INEL	., RAD-HARD B	ASED ON TYPE STRH100N6			
Number:	5205/022		Issue:	-	7				
Other documen	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers	Appendix (for STM)								
Original wording	j :								
As per current p	oublished specification	n							
Proposed wordi	ng:								
the listed ESCO	As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix								
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specific	ation: Para. 8,	, Tes	st Methods and	Procedures.			
For qualification replacement tes • No. 20400, Int • 2072: for Tran		ons may be u on (Para. 8.2) aged Variants	sed in place o): may be repl	of the	e following ESC	ualified components, the following C Basic Specifications: 50 Test Method:			
	ver MOSFET Die and		ariants (to be	cont	firmed by ST by	2020 week 35)			
• No. 20500, Ex	No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)								



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMEN	TED		
• No. 20900, Radiogra Method 2076 (all type	• •	ion of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	DC	DCUMENT	CHANGE REQUEST		
DCR number	1365	Changes ree	quired for: Gen	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED				occicianat		
Title:	Diodes, Power Red	ctifier, High Eff	iciency Fast Rec	covery , based or	n Type BYV 54-200		
Number:	5103/031		Issue:	10			
Other documen	ts affected:			-			
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current	published specificati	on					
Proposed word	ing:						
the listed ESCO		ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations		
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	eneric Specifica	ation: Para. 8, Te	est Methods and	Procedures.		
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants							
	ver MOSFET Die an		·				
• No. 20500, E>	kternal Visual Inspec	tion (Para. 8.6	b): may be replace	ed by: MIL-STD	-750 Test Method 2071 (all types)		
• No. 20900, Ra Method 2076 (a	• • •	on of Electroni	c Components (Para. 8.14): may	be replaced by MIL-STD-750 Test		
STD-750 Metho	 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 						
Justification:							

	ESC	C		DC	CUMENT	CHANGE REQUEST						
DCR number	1365	Changes re	quired for:	Gen	eral	Originator: Steve Thacker						
Date: 2024/02	/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat						
Status: IMPLE	Status: IMPLEMENTED											
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.											
5000 to remove Basic specificat	and replace the vari	ous ESCC Ba 00 i.e. Infined	asic specific on, Cobharr	catior n. Acc	ns; some Manufa cordingly STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec rious Detail Specs supported by STM.						
Title:	Diode, Rectifier, Hig	h Voltage ba	sed on type	es ST	TH40200 and ST	TH60200						
Number:	5103/033		Issue:		2							
Other documen	ts affected:											
Page:												
as applicable												
Paragraph:												
Manufacturers	Appendix (for STM)											
Original wording	j :											
As per current p	published specificatio	n										
Proposed wordi	ng:											
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix												
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.												
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be u on (Para. 8.2) aged Variants Variants	sed in place): may be re	e of th eplace	ne following ESC ed by MIL-STD-7							
	ver MOSFET Die and		·									
• No. 20500, Ex	No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)											



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENT	ΓED		
• No. 20900, Radiogra Method 2076 (all type	• •	on of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	DOCUMENT CHANGE REQUE								
DCR number	1365	Changes re	eral	Originator: Steve Thacker					
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLE	EMENTED				ocorolanda				
Title:	Transistors, Low P	ower, Comple	mentary NPN/PN	NP Based on type	e 2ST3360				
Number:	5207/009		Issue:	4					
Other documen	ts affected:		-						
Page:									
as applicable									
Paragraph:									
Manufacturers	Appendix (for STM)								
Original wording	g:								
As per current p	oublished specificati	on							
Proposed wordi	ing:								
the listed ESCO		ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations				
ITEMS AFFEC [®] Para. 2.1.1, De	TED viations from the Ge	neric Specific	ation: Para. 8, Te	est Methods and	Procedures.				
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)									
			·		-750 Test Method 2071 (all types)				
	adiographic Inspection	·			be replaced by MIL-STD-750 Test				
STD-750 Metho	 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 								
Justification:									

	ESC	C		DC	CUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for: (Gene	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED						
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.						
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.						
Title:	TRANSISTORS, PO	OWER, MOSI	ET, N-CHA	NNE	L, RAD-HARD B	ASED ON TYPE STRH40N6	
Number:	5205/024		Issue:		7		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current p	oublished specification	n					
Proposed wordi	ng:						
the listed ESCO		s, all under E	SCC Generic			ethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC ⁻ Para. 2.1.1, De	TED viations from the Ger	neric Specific	ation: Para. 8	8, Te	est Methods and	Procedures.	
For qualification replacement tes • No. 20400, Int • 2072: for Tran	-	ons may be u on (Para. 8.2) aged Variants	sed in place): may be rep	of th	e following ESC	ualified components, the following C Basic Specifications: 50 Test Method:	
	ver MOSFET Die and						
• No. 20500, E>	ternal Visual Inspect	ion (Para. 8.6	6): may be re	plac	ed by: MIL-STD-	750 Test Method 2071 (all types)	



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMEN	TED		
• No. 20900, Radiogra Method 2076 (all type	• •	ion of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	D	OCUMEN	T CHANGE REQUEST	
DCR number	1365	Changes required for	or: Ger	neral	Originator: Steve Thacker	
Date: 2024/02		Date sent: 2020/07	/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE						
Title:	Transistors High Po	wer NPN, based on t	ype BU	X77		
Number:	5203/016	Issue:		6		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current p	published specification	n				
Proposed wordi	ing:					
the listed ESCO		s, all under ESCC Ge			Methods by Suitable Alternatives review, 5000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De		neric Specification: Pa	ara. 8, T	est Methods a	nd Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)						
• No. 20500, Ex	ternal Visual Inspec	ion (Para. 8.6): may l	be repla	ced by: MIL-ST	D-750 Test Method 2071 (all types)	
	adiographic Inspectic			-	ay be replaced by MIL-STD-750 Test	
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.					
Justification:						

	ESC	C		DC	CUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for: C	Gen	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED						
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.						
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.						
Title:	Diodes Silicon Swite	ching, based	on types 1N6	6639), 1N6640 and 1№	N6641	
Number:	5101/027		Issue:		5		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current p	oublished specificatio	n					
Proposed wordi	ing:						
the listed ESCO		s, all under E	SCC Generic	-		ethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ger	neric Specific	ation: Para. 8	B, T€	est Methods and	Procedures.	
For qualification replacement tes • No. 20400, Int • 2072: for Tran	•	ons may be u on (Para. 8.2) aged Variants	sed in place : may be rep	of th	e following ESC	ualified components, the following C Basic Specifications: 50 Test Method:	
• 2069: for Pov	ver MOSFET Die and	d packaged V	·				
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	6): may be re	plac	ed by: MIL-STD-	750 Test Method 2071 (all types)	



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMEN	TED		
• No. 20900, Radiogra Method 2076 (all type	• •	ion of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C		DC	OCUMEN	T CHANGE REQUEST
DCR number	1365	Changes rec	uired for: (Gen	eral	Originator: Steve Thacker
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat
Status: IMPLE	EMENTED					
Title:	Matched Dual Tran	sistors NPN, b	ased on typ	e 21	N3350	
Number:	5207/003		Issue:		5	
Other documen	ts affected:				-	
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current p	published specification	on				
Proposed wordi	ing:					
the listed ESCC		ns, all under ES	SCC Generio			Methods by Suitable Alternatives review, 5000, shall have the following deviations
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specifica	ition: Para. 8	B, T€	est Methods ar	nd Procedures.
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)						
					-	D-750 Test Method 2071 (all types)
	adiographic Inspectio	•	· -		-	ay be replaced by MIL-STD-750 Test
STD-750 Metho	od 2077 (for Power N	MOSFET Die a	nd package	d Va	ariants).	Para. 8.3 & 9.5): may be replaced by MIL- ar Detail Specifications that specifically
Justification:						

Number: 5201/003 Issue: 5 Other documents affected:		ESC	C	D	OCUMENT	CHANGE REQUEST		
Status: IMPLEMENTED Secretariat The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear: preferenced for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specifications in ESCC No. 5000 i.e. Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly, MID STMs preferred change to apply the MIL speciatematives, as is reflected in this DCR, is to be implemented by changes to the various Detail Species supported by STM. Title: Transistors Low Power NPN, based on type 2N2219A Number: 5201/003 Issue: 5 Other documents affected:	DCR number	1365	Changes required	for: Ger	neral	Originator: Steve Thacker		
The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the B4th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method. Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to ratin these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham) Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly, Mg STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM. Title: Transistors Low Power NPN, based on type 2N2219A Number: 5 201/003 Issue: 5 Other documents affected: Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As per current published specification As proceeding Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS	Date: 2024/02	/29	Date sent: 2020/0)7/28		-		
Adth PSWG MoM, was: STM answer is clear : preference for ML specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method. Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred thange to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM. Title: Transistors Low Power NPN, based on type 2N2219A Number: 5201/003 Issue: 5 Other documents affected: Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS	Status: IMPLE	MENTED						
5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM. Title: Transistors Low Power NPN, based on type 2N2219A Number: 5201/003 Issue: 5 Other documents affected: Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maticance, or procurement of qualification runqualified components, the following	84th PSWG Mo STM answer is Accordingly, the	84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL						
Number: 5201/003 Issue: 5 Other documents affected:	5000 to remove Basic specificat	and replace the vari	ous ESCC Basic sp 00 i.e. Infineon, Co	becificatio bham. Ac	ns; some Manufa cordingly STMs p	cturers preferred to retain these ESCC preferred change to apply the MIL spec		
Other documents affected: Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Title:	Transistors Low Pov	ver NPN, based on	type 2N2	219A			
Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Number:	5201/003	Issue	:	5			
as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Other document	ts affected:						
as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following								
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Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	as applicable							
Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Paragraph:							
As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Manufacturers /	Appendix (for STM)						
Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	Original wording	j:						
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Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following	the listed ESCC	Detail Specifications	s, all under ESCC C					
For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following								
 replacement test method specifications may be used in place of the following ESCC Basic Specifications: No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: 2072: for Transistor Die and packaged Variants 2078: for Diode Die and packaged Variants 	For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	and qualification ma at method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be used in on (Para. 8.2): may aged Variants Variants	place of t be replac	the following ESC ced by MIL-STD-7	C Basic Specifications: '50 Test Method:		
 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35) No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types) 								



DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENT	ΓED		
• No. 20900, Radiogra Method 2076 (all type	• •	on of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	DC	DCUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for: Gen	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED				Secretariat	
Title:	Diodes, Silicon, Po	wer Schottky I	Rectifier based o	on Type 1N5822L	J	
Number:	5106/020		Issue:	5		
Other documen	ts affected:		-	-		
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current	published specificati	on				
Proposed word	ing:					
the listed ESCO		ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specific	ation: Para. 8, Te	est Methods and	Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)						
			·			
• No. 20900, Ra	 No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types) No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 					
STD-750 Metho	 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 					
Justification:						

	ESC	C		DC	CUMENT	CHANGE REQUEST	
DCR number	1365	Changes red	quired for:	Gene	eral	Originator: Steve Thacker	
Date: 2024/02	/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	MENTED						
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.						
5000 to remove Basic specificat	and replace the vari ions in ESCC No. 50	ous ESCC Ba 00 i.e. Infined	asic specific on, Cobham	cation	s; some Manufactoria some STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec rious Detail Specs supported by STM.	
Title:	Diodes, Power Rect	ifier, Schottky	/ Barrier, ba	ased	on type STPS201	100	
Number:	5106/016		Issue:		10		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers /	Appendix (for STM)						
Original wording	j :						
As per current p	published specificatio	'n					
Proposed wordi	ng:						
the listed ESCC		s, all under E	SCC Gener			ethods by Suitable Alternatives review, 000, shall have the following deviations	
	ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.						
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be us on (Para. 8.2) aged Variants I Variants	sed in place : may be re	e of th eplace	e following ESC ed by MIL-STD-7		
	ver MOSFET Die and		·				
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	5): may be r	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)	

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DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENT	ED		ocorotanat
 • No. 20900, Radiogra Method 2076 (all type:	• •	on of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	DC		NT CHANGE REQUEST	
DCR number	1365	Changes required for:	Gen	eral	Originator: Steve Thacker	
Date: 2024/02		Date sent: 2020/07/28	3		Organisation: ESCC Executive Secretariat	
Status: IMPLE						
Title:	Transistors Low Po	wer NPN, based on type	e 2N3	700		
Number:	5201/004	Issue:		8		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current p	oublished specification	on				
Proposed wordi	ing:					
the listed ESCC		s, all under ESCC Gene			est Methods by Suitable Alternatives review, lo. 5000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De		neric Specification: Para	a. 8, T	est Methods a	and Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)						
					STD-750 Test Method 2071 (all types)	
	adiographic Inspectio			·	may be replaced by MIL-STD-750 Test	
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.					
Justification:						

	ESC	C	[OCUMENT	CHANGE REQUEST		
DCR number	1365	Changes rec	uired for: G	eneral	Originator: Steve Thacker		
Date: 2024/02	/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat		
Status: IMPLE	MENTED						
The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.							
Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.							
Title:	Transistors High Po	wer NPN, bas	ed on type 2	N5154			
Number:	5203/010		lssue:	9			
Other document	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers /	Appendix (for STM)						
Original wording	j:						
As per current p	oublished specificatio	n					
Proposed wordi	ng:						
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix							
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.							
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be us on (Para. 8.2) aged Variants Variants	ed in place o : may be repl	f the following ESC aced by MIL-STD-7			
	ver MOSFET Die and		·				
- INU. 20000, EX	aemai visuai inspect	iuii (Faia. 0.0	j. may be rep	aceu by. MIL-SID	-750 Test Method 2071 (all types)		

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DCR number	1365	Changes required for: General	Originator: Steve Thacker			
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat			
Status: IMPLEMEN	TED					
• No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).						

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	<u>ESC</u>	C	DC	DCUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for: Gen	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent:	2020/07/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED				Jecietanat	
Title:	Diode, Power, Scl	hottky Rectifier	, based on Type	STPS80A45C ar	nd STPS40A45C	
Number:	5106/024		Issue:	2		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)				
Original wording	g:					
As per current	published specifica	tion				
Proposed word	ing:					
the listed ESCO		ons, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.						
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants						
• 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)						
• No. 20500, E>	kternal Visual Inspe	ection (Para. 8.6	6): may be replac	ced by: MIL-STD	-750 Test Method 2071 (all types)	
 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 						
 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 						
Justification:						

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DCR number	1365	Changes ree	quired for:	Gen	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED							
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.							
Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.								
Title:	Diodes Switching, t	based on type	s 1N5802, 1	N58	04, 1N5806, 1N5	802US, 1N5804US, 1N5806US and		
Number:	5101/014		Issue:		5			
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	g:							
As per current	oublished specification	on						
Proposed word	ng:							
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix								
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.								
For qualification replacement tes • No. 20400, In • 2072: for Tra	DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants							
• 2069: for Pov	ver MOSFET Die and	d packaged Va						
• No. 20500, E>	ternal Visual Inspec	tion (Para. 8.6	5): may be re	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)		



DCR number	1365	Changes required for: General	Originator: Steve Thacker			
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat			
Status: IMPLEMEN	ΓED					
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• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

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Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

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DCR number	1365	Changes required for:	Gen	eral	Originator: Steve Thacker	
Date: 2024/02		Date sent: 2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED					
Title:	Transistors Low Po	wer NPN, based on type	2N22	222A		
Number:	5201/002	Issue:		10		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current p	published specification	on				
Proposed wordi	ng:					
the listed ESCC		s, all under ESCC Gene			Methods by Suitable Alternatives review, 5000, shall have the following deviations	
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• No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)						
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Justification:						

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	ESC	C		DC	DCUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for:	Gen	eral	Originator: Steve Thacker	
Date: 2024/02	/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	MENTED						
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Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.							
Title:	Transistors Low Por	wer NPN, bas	ed on type	2N24	184		
Number:	5201/001		lssue:		8		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	j:						
As per current p	oublished specification	n					
Proposed wordi	ng:						
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix							
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	ver MOSFET Die and					·	
• No. 20500, Ex	tternal Visual Inspect	ion (Para. 8.6): may be r	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)	



DCR number	1365	Changes required for: General	Originator: Steve Thacker			
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat			
Status: IMPLEMEN	ΓED					
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• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

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	ESC	C	DC	DCUMENT	CHANGE REQUEST	
DCR number	r 1365 Changes required for: General				Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED				Secretariat	
Title:	Diodes Power Re	ctifier Schottky	Barrier based o	n Type STPS401	100	
Number:	5106/019		Issue:	9		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM))				
Original wording	g:					
As per current	published specificat	ion				
Proposed word	ing:					
the listed ESCO	•	ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the G	eneric Specific	ation: Para. 8, T	est Methods and	Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants						
	ver MOSFET Die a		·			
		·		·	-750 Test Method 2071 (all types)	
 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 						
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Justification:						

	ESC	C	I	DC	CUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	quired for: C	Gene	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED						
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Title:	Diodes Silicon Swite	ching, based	on types 1N6	638	s, 1N6642 and 1N	N6643	
Number:	5101/026		Issue:		6		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current p	oublished specificatio	n					
Proposed wordi	ing:						
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix							
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.							
For qualification replacement tes • No. 20400, Int • 2072: for Tran	•	ons may be u on (Para. 8.2) aged Variants	sed in place (): may be rep	of th	e following ESC	ualified components, the following C Basic Specifications: 50 Test Method:	
• 2069: for Pov	ver MOSFET Die and	d packaged V					
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	6): may be re	plac	ed by: MIL-STD-	750 Test Method 2071 (all types)	



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Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat			
Status: IMPLEMEN	ΓED					
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DCR number	1365	Changes rec	quired for: Gen	eral	Originator: Steve Thacker	
Date: 2024/02	2/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED				ocorolandi	
Title:	Matched Dual Trar	nsistors NPN, b	based on types 2	2N2919/2N2920 a	and 2N2920A	
Number:	5207/002		Issue:	10		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current p	published specificati	on				
Proposed wordi	ng:					
the listed ESCC	• •	ns, all under E	SCC Generic Sp		ethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	eneric Specifica	ation: Para. 8, T	est Methods and	Procedures.	
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• No. 20500, Ex	• No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)					
• No. 20900, Ra Method 2076 (a		on of Electroni	c Components (Para. 8.14): may	be replaced by MIL-STD-750 Test	
STD-750 Metho	 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 					
Justification:						

	ESC	C	C	OCUMENT	CHANGE REQUEST				
DCR number	1365	Changes req	uired for: Ge	eneral	Originator: Steve Thacker				
Date: 2024/02	/29	Date sent: 20	020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLE	MENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
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Title:	Transistors Low Pov	ver PNP, base	ed on type 2N	2907A					
Number:	5202/001	I	ssue:	10					
Other document	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers /	Appendix (for STM)								
Original wording	j:								
As per current p	oublished specificatio	n							
Proposed wordi	ng:								
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	ver MOSFET Die and		·						
- INU. 20000, EX	liemai visuai inspect	iuli (Para. 8.6)	. may be rep	aceu by: MIL-STD	-750 Test Method 2071 (all types)				



DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
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	ESC		DC	DCUM	ENT	CHANGE REQUEST	
DCR number	c 1365 Changes required for: General					Originator: Steve Thacker	
Date: 2024/02		Date sent: 2020/07/28	3			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED						
Title:	Transistors Matche	d Dual PNP, based on t	/pes 2	2N3810 an	d 2N3	811	
Number:	5207/005	Issue:		8			
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current p	published specificati	on					
Proposed wordi	ing:						
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STD-750 Metho	 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 						
Justification:							

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5000 to remove Basic specificat	and replace the vari	ous ESCC Ba 00 i.e. Infined	asic specifi on, Cobhan	catior n. Acc	ns; some Manufa cordingly STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec rious Detail Specs supported by STM.			
Title:	Diode, Silicon, Powe	er Rectifier, S	Schottky Ba	arrier,	based on Type S	STPS1045			
Number:	5106/017		Issue:		7				
Other document	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers /	Appendix (for STM)								
Original wording	j :								
As per current p	published specificatio	n							
Proposed wordi	ng:								
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	ver MOSFET Die and								
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	5): may be r	replac	ed by: MIL-STD-	750 Test Method 2071 (all types)			



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	ESC		D	OCUMI	ENT	CHANGE REQUEST	
DCR number	1365	Changes require	red for: Ge	eneral		Originator: Steve Thacker	
Date: 2024/02		Date sent: 202	20/07/28			Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED						
Title:	Transistors, Low P	ower, NPN, base	d on type 2	ST15300			
Number:	5201/020	lss	sue:	1			
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current	published specificati	on					
Proposed word	ing:						
the listed ESCO		ns, all under ESC	C Generic			ethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specificatio	n: Para. 8,	Test Method	ds and	Procedures.	
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants							
	 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35) No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types) 						
				·			
• No. 20900, Ra Method 2076 (a	• • •		omponents	5 (Fala. 8.14	. may	be replaced by MIL-STD-750 Test	
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.						
Justification:							

	ESC	C	[DC	CUMENT	CHANGE REQUEST			
DCR number	1365	Changes rec	quired for: G	Gene	eral	Originator: Steve Thacker			
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat			
Status: IMPLE	EMENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
5000 to remove Basic specificat	e and replace the var tions in ESCC No. 50	ious ESCC Ba 000 i.e. Infined	asic specifica n, Cobham.	ation Acc	s; some Manufa ordingly STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec prious Detail Specs supported by STM.			
Title:	TRANSISTORS, PO	OWER, MOSF	ET, N-CHAN	NNE	L, RAD-HARD B	BASED ON TYPE STRH8N10			
Number:	5205/023		Issue:		7				
Other documen	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers	Appendix (for STM)								
Original wording	g:								
As per current p	oublished specification	on							
Proposed wordi	ng:								
the listed ESCO	As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix								
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.									
For qualification replacement tes • No. 20400, Int • 2072: for Tran	•	ons may be us ion (Para. 8.2) aged Variants	ed in place of the sed in place of the sed in place of the sed of	of th	e following ESC	ualified components, the following C Basic Specifications: 50 Test Method:			
	ver MOSFET Die and		ariants (to be	e cor	ifirmed by ST by	2020 week 35)			
• No. 20500, E>	ternal Visual Inspec	tion (Para. 8.6): may be re	plac	ed by: MIL-STD-	750 Test Method 2071 (all types)			



DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
Status: IMPLEMEN	ΓED							
No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).								

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	DOCUMENT CHANGE REQUEST							
DCR number	1365	Changes required for: 0	General	Originator: Steve Thacker				
Date: 2024/02		Date sent: 2020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLE	MENTED							
Title:	Transistors, Power	, MOSFET, N-Channel, RA	D-HARD, based on	Type STRH100N10FSY3				
Number:	5205/021	Issue:	8					
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	j :							
As per current p	published specification	on						
Proposed wordi	ng:							
the listed ESCC		ns, all under ESCC Generic	-	Aethods by Suitable Alternatives review, 000, shall have the following deviations				
ITEMS AFFEC Para. 2.1.1, Dev		neric Specification: Para. 8	3, Test Methods and	Procedures.				
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants								
• 2069: for Pow	ver MOSFET Die an	d packaged Variants (to be	e confirmed by ST b	y 2020 week 35)				
• No. 20500, Ex	ternal Visual Inspec	tion (Para. 8.6): may be re	placed by: MIL-STD	-750 Test Method 2071 (all types)				
	 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 							
• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.								
Justification:								

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	ESC	C		DC	CUMENT	CHANGE REQUEST		
DCR number	1365	Changes re	quired for:	Gen	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED							
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.							
5000 to remove Basic specificat	e and replace the var tions in ESCC No. 50	ious ESCC Ba)00 i.e. Infined	asic specific on, Cobham.	ation . Acc	ns; some Manufa cordingly STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec rious Detail Specs supported by STM.		
Title:	Diode, Power, Scho	ottky Rectifier,	Surface Mo	ount l	based on Type S	TPS80A150, STPS60A150		
Number:	5106/023		Issue:		4			
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	g:							
As per current	published specification	on						
Proposed word	ing:							
the listed ESCO	As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix							
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.								
For qualification replacement tes • No. 20400, In • 2072: for Tra	•	ons may be u on (Para. 8.2) aged Variants	sed in place): may be re	of th	ne following ESC	ualified components, the following C Basic Specifications: 50 Test Method:		
• 2069: for Pov	ver MOSFET Die and	d packaged V	·					
• No. 20500, E>	cternal Visual Inspect	tion (Para. 8.6	6): may be re	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)		



DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
Status: IMPLEMEN	ΓED							
No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).								

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	DC	DCUMENT	CHANGE REQUEST		
DCR number	ber 1365 Changes required for: General Originator: Steve Thacker						
Date: 2024/02	2/29	Date sent:	2020/07/28		Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED				Georgianat		
Title:	Diode, Silicon, Po	wer Schottky R	ectifier, based o	n Type 1N5819			
Number:	5106/021		Issue:	5			
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current	published specificat	ion					
Proposed word	ing:						
the listed ESCO	•	ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations		
ITEMS AFFEC Para. 2.1.1, De	TED viations from the G	eneric Specific	ation: Para. 8, T	est Methods and	Procedures.		
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)							
			·				
 No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types) No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 							
 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 							
Justification:							

	ESC	C	[DOCUMENT	CHANGE REQUEST				
DCR number	1365	Changes rec	uired for: G	eneral	Originator: Steve Thacker				
Date: 2024/02	/29	Date sent: 2	2020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLE	MENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.								
Title:	Transistors Low Pov	wer NPN, bas	ed on type 21	N2369A					
Number:	5201/006		Issue:	6					
Other document	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers /	Appendix (for STM)								
Original wording	j:								
As per current p	oublished specificatio	n							
Proposed wordi	ng:								
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix									
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.									
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be us on (Para. 8.2) aged Variants Variants	ed in place o : may be repl	f the following ESC aced by MIL-STD-					
	ver MOSFET Die and		·	-					
• No. 20500, Ex	ternal visual Inspect	ion (Para. 8.6): may be rep	naced by: MIL-STD	0-750 Test Method 2071 (all types)				



DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
Status: IMPLEMEN								
No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).								

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

DOCUMENT CHANGE REQUEST								
DCR number	1365 Changes required for: General Originator: Steve Thacker							
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED					occicianat		
Title:	TRANSISTORS, P	OWER, MOSF	ET, P-CHAN	INE	L, RAD-HARD E	BASED ON TYPE STRH40P10		
Number:	5205/025		lssue:		7			
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	g:							
As per current p	published specification	on						
Proposed wordi	ng:							
the listed ESCC		s, all under E	SCC Generic			lethods by Suitable Alternatives review, 000, shall have the following deviations		
ITEMS AFFEC ⁻ Para. 2.1.1, De	TED viations from the Ge	neric Specifica	ation: Para. 8	, Te	est Methods and	Procedures.		
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)								
						-750 Test Method 2071 (all types)		
• No. 20900, Ra Method 2076 (a	• • •	DI OT Electroni	component	ts (I	rara. 8.14): may	be replaced by MIL-STD-750 Test		
 No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it. 								
Justification:								

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	ESC	C		DC	DCUMENT	CHANGE REQUEST			
DCR number	1365	Changes ree	quired for:	Gen	eral	Originator: Steve Thacker			
Date: 2024/02		Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat			
Status: IMPLE	MENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
5000 to remove Basic specificat	and replace the vari	ous ESCC Ba 00 i.e. Infined	asic specifio on, Cobharr	catior n. Acc	ns; some Manufac cordingly STMs p	neon, Cobham) supporting ESCC No. cturers preferred to retain these ESCC referred change to apply the MIL spec rious Detail Specs supported by STM.			
Title:	Transistors High Vo	ltage NPN, ba	ased on typ	e 2N	5551				
Number:	5201/019		Issue:		9				
Other documen	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers	Appendix (for STM)								
Original wording	j :								
As per current p	oublished specificatio	'n							
Proposed wordi	ng:								
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix									
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.									
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be us on (Para. 8.2) aged Variants I Variants	sed in place and may be re	e of th eplace	ne following ESC ed by MIL-STD-7				
	ver MOSFET Die and		·						
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	5): may be r	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)			

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DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
Status: IMPLEMEN								
No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).								

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

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Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	DC	DCUMENT	CHANGE REQUEST	
DCR number	1365	Changes re	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent:	2020/07/28		Organisation: ESCC Executive Secretariat	
Status: IMPLE	EMENTED				Occidianat	
Title:	Diode, Silicon, Pov	ver Rectifier, S	Schottky Barrier,	based on Type S	STPS6045	
Number:	5106/018		Issue:	8		
Other documen	ts affected:					
Page:						
as applicable						
Paragraph:						
Manufacturers	Appendix (for STM)					
Original wording	g:					
As per current	published specificat	ion				
Proposed word	ing:					
the listed ESCO	•	ns, all under E	SCC Generic Sp		lethods by Suitable Alternatives review, 000, shall have the following deviations	
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	eneric Specific	ation: Para. 8, T	est Methods and	Procedures.	
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	ver MOSFET Die ar		·			
• No. 20500, Ex	kternal Visual Inspe	ction (Para. 8.6	6): may be replac	ced by: MIL-STD	-750 Test Method 2071 (all types)	
	 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 					
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.					
Justification:						

	ESC	C		DC	CUMENT	CHANGE REQUEST		
DCR number	1365	Changes re	quired for: (Gen	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED							
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.							
5000 to remove Basic specificat	Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; some Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL spec alternatives, as is reflected in this DCR, is to be implemented by changes to the various Detail Specs supported by STM.							
Title:	TRANSISTORS, PO	OWER, MOSI	ET, P-CHA	NNE	L, RAD-HARD B	ASED ON TYPE STRH12P10		
Number:	5205/029		Issue:		7			
Other documen	ts affected:							
Page:								
as applicable								
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording	g:							
As per current p	oublished specification	n						
Proposed wordi	ng:							
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix								
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For qualification replacement tes • No. 20400, Int • 2072: for Tran	-	ons may be u on (Para. 8.2) aged Variants	sed in place): may be rep	of th	ne following ESC	ualified components, the following C Basic Specifications: 50 Test Method:		
	ver MOSFET Die and							
• No. 20500, E>	ternal Visual Inspect	tion (Para. 8.6	6): may be re	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)		



DCR number	1365	Changes required for: General	Originator: Steve Thacker					
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat					
Status: IMPLEMEN								
No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types).								

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

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Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	D	OCUMEN	IT CHANGE REQUEST		
DCR number	1365	Changes required	d for: Ge	eneral	Originator: Steve Thacker		
Date: 2024/02	/29	Date sent: 2020/	07/28		Organisation: ESCC Executive Secretariat		
Status: IMPLE	MENTED						
Title:	Transistors Low Po	wer PNP, based on	type 2N	5401			
Number:	5202/014	Issue	e:	9			
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current p	published specification	ิวท					
Proposed wordi	ng:						
the listed ESCC		s, all under ESCC			t Methods by Suitable Alternatives review, . 5000, shall have the following deviations		
ITEMS AFFEC Para. 2.1.1, De	TED viations from the Ge	neric Specification:	Para. 8,	Test Methods a	nd Procedures.		
DESCRIPTION OF DEVIATIONS For qualification and qualification maintenance, or procurement of qualified or unqualified components, the following replacement test method specifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2078: for Diode Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)							
• No. 20900, Ra	 No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types) No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). 						
STD-750 Metho	• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.						
Justification:							

	ESC	C		DC	CUMENT	CHANGE REQUEST			
DCR number	1365	Changes ree	quired for:	Gen	eral	Originator: Steve Thacker			
Date: 2024/02		Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat			
Status: IMPLE	MENTED								
84th PSWG Mo STM answer is Accordingly, the	The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was: STM answer is clear : preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.								
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Title:	Transistors High Po	wer NPN, ba	sed on type	s 2N	3439 and 2N3440	0			
Number:	5203/011		Issue:		5				
Other document	ts affected:								
Page:									
as applicable									
Paragraph:									
Manufacturers /	Appendix (for STM)								
Original wording	j :								
As per current p	published specificatio	n							
Proposed wordi	ng:								
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix									
ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures.									
For qualification replacement tes • No. 20400, Int • 2072: for Tran • 2078: for Diod	st method specification ernal Visual Inspection nsistor Die and packa de Die and packaged	ons may be us on (Para. 8.2) aged Variants Variants	sed in place): may be re	e of th eplace	ne following ESC ed by MIL-STD-7				
	ver MOSFET Die and								
• No. 20500, Ex	ternal Visual Inspect	ion (Para. 8.6	6): may be r	eplac	ed by: MIL-STD-	750 Test Method 2071 (all types)			



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DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENT	ſED	Coordianat	
• No. 20900, Radiogra Method 2076 (all type	• •	on of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

• No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL-STD-750 Method 2077 (for Power MOSFET Die and packaged Variants).

Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	Ċ		DC	DCUME	NT	CHANGE REQUEST
DCR number	1365	1365 Changes required for: General			eral		Originator: Steve Thacker
Date: 2024/02	2/29	Date sent: 2	020/07/28				Organisation: ESCC Executive Secretariat
Status: IMPLE	EMENTED						
Title:	Transistors Low Po	ower RF NPN, b	based on ty	pe 2	N3019		
Number:	5201/011	I	ssue:		6		
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current published specification							
Proposed wordi	Proposed wording:						
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• No. 20500, External Visual Inspection (Para. 8.6): may be replaced by: MIL-STD-750 Test Method 2071 (all types)							
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Justification:							

Other documents affected: Page: as applicable Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification and qualifications may be used in place of the following ESCC Basic Specifications: • No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Test Method: • 2072: for Transistor Die and packaged Variants • 2069: for Power MOSFET Die and packaged Variants (to be confirmed by ST by 2020 week 35)		ESC	C	D	OCUMENT	CHANGE REQUEST				
Status: IMPLEMENTED Secretariat The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the Ath PSWG MoM, was STM answer is clear: preference for MIL specifications except for radiation test method. Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method. Note: there was no consensus between the 3 ESCCQPL Manufacturers (STM, Infineon, Cobham) supporting ESCC No. 5000 to remove and replace the various ESCC Basic specifications; som Manufacturers preferred to retain these ESCC Basic specifications in ESCC No. 5000 i.e. Infineon, Cobham. Accordingly STMs preferred change to apply the MIL specifications is a stated in this DCR, is to be implemented by changes to the various Detail Species supported by STM. Title: Transistors Low Power PNP, based on type 2N4033 Number: S202008 Issue: 7 Other documents affected: Paragraph: Manufacturers Appendix (for STM) Original wording: As per current published specification Proposed wording: As per ourrent published specifications, and under SCC Generic Specification No. 5000, shall have the following deviations added to the STMCROELECTRONICS (F) appendix ITEMS AFFECTED Para. 2.1.1, Deviations from the Generic Specification: Para. 8, Test Methods and Procedures. DESCRIPTION OF DEVIATIONS For qualification maintenance, or procurement of qualified or unqualified components, the following replacement termethod specifications Proposed to the Disolog and packaged Variants 2.0276. The Disol Devia Appendiation and qualified appendiations 2.075. Transistor Devia Appendiation maintenance, or procurement of qualified or unqualified components, the following replacement termethod specifications and under the specifications: No. 20400, Internal Visual Inspection (Para. 8.2): may be replaced by MIL-STD-750 Te	DCR number	1365	Changes requi	red for: Gei	neral	Originator: Steve Thacker				
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DCR number	1365	Changes required for: General	Originator: Steve Thacker
Date: 2024/02/29		Date sent: 2020/07/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENT	ΓED		
• No. 20900, Radiogra Method 2076 (all type	• •	on of Electronic Components (Para. 8.14): may	be replaced by MIL-STD-750 Test

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Note: the deviation on ESCC No. 21400 shall only be included for those particular Detail Specifications that specifically refer to it.

Justification:

The conclusion of the PSWG task ESCC improvement - ESCC conversion to MIL for Manufacturer STM, as stated in the 84th PSWG MoM, was:

STM answer is clear : preference for MIL specifications except for radiation test method.

Accordingly, the various referenced ESCC test methods should each be made replaceable by the appropriate MIL specification test method.

	ESC	C	D	OCUMENT	CHANGE REQUEST		
DCR number	1365 Changes required for: General			neral	Originator: Steve Thacker		
Date: 2024/02		Date sent: 2020/0)7/28		Organisation: ESCC Executive Secretariat		
Status: IMPLE							
Title:	Transistors High Po	ower PNP, based on	type 2N5	5153			
Number:	5204/002	Issue	:	9			
Other documen	ts affected:						
Page:							
as applicable							
Paragraph:							
Manufacturers	Appendix (for STM)						
Original wording	g:						
As per current published specification							
Proposed wording:							
As part of the ESCC System Improvement Review - Replacing Referenced Test Methods by Suitable Alternatives review, the listed ESCC Detail Specifications, all under ESCC Generic Specification No. 5000, shall have the following deviations added to the STMICROELECTRONICS (F) appendix							
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Justification:	Justification:						

	ESC	C		DC	CUMENT	CHANGE REQUEST		
DCR number	1365	Changes ree	quired for: 0	Gen	eral	Originator: Steve Thacker		
Date: 2024/02	2/29	Date sent: 2	2020/07/28			Organisation: ESCC Executive Secretariat		
Status: IMPLE	EMENTED							
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Title:	Diode, Rectifier, Hig	gh Voltage, Su	urface Mount	t Bas	sed on type STTI	H60400		
Number:	5103/032		Issue:	3				
Other documen	ts affected:							
Page:								
as applicable	as applicable							
Paragraph:								
Manufacturers	Appendix (for STM)							
Original wording:								
As per current published specification								
Proposed wording:								
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	DOCUMENT CHANGE REQUEST							
DCR number	Originator: Steve Thacker							
Date: 2024/02/29		Date sent: 2020/07/28		Organisation: ESCC Executive Secretariat				
Status: IMPLEME	NIED							
Method 2076 (all ty • No. 21400, Scann STD-750 Method 2	 No. 20900, Radiographic Inspection of Electronic Components (Para. 8.14): may be replaced by MIL-STD-750 Test Method 2076 (all types). No. 21400, Scanning Electron Microscope Inspection of Semiconductor Dice (Para. 8.3 & 9.5): may be replaced by MIL- STD-750 Method 2077 (for Power MOSFET Die and packaged Variants). 							
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Attachments:								
N/A								
Modifications:								
Remove the replacement MIL method 2069, applicable to ESCC No. 20400, from this DCR: i.e. delete: *2069: for Power MOSFET Die and package Variants (confirmed by ST)								
Approval signature:								
Alistan Rein								
Date signed:								
2024-02-29	2024-02-29							